

Trench MOS Barrier Schottky Rectifier - 30Amp 300Volt

Features

- Plastic package has Underwriters Laboratory Flammability Classifications 94V-0
- High Junction Temperature Capability
- Low forward voltage, high current capability
- High surge capacity
- Low power loss, high efficiency
- Halogen-Free

Application

- AC/DC Switching Adaptor and other Switching Power Supply

Absolute maximum ratings

Symbol	Ratings	Unit	Conditions
IF(AV)	30	A	Average Forward Current
VRRM	300	V	Repetitive Peak Reverse Voltage
IFSM	200	A	Peak Forward Surge Current
VF	0.85	V	Forward Voltage Drop
Tj, Tstg	-65 to +150	°C	Operating and Storage Temperature

Electrical characteristics

Parameters	Symbol	Ratings	Conditions
Maximum Instantaneous Forward Voltage	VF	1.00V	Per Leg at IF = 15A Tc = 25°C
		0.85V	Tc = 125°C
Maximum Reverse Leakage Current	IR	0.05mA	Per Leg at VR = 300V Tc = 25°C
		10mA	Tc = 125°C
Typical Thermal Resistance, Junction to Case	Rθ(j-c)	2.2 °C/W	Per Leg TO-220AB
		4.5 °C/W	ITO-220AB

Note : 1. Mounted on P.C.B with copper pad size 20mm x 30mm, thickness 1.5mm

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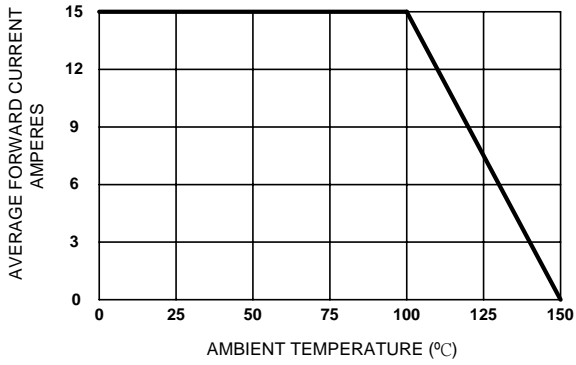


Figure 1. Forward Current Derating Curve

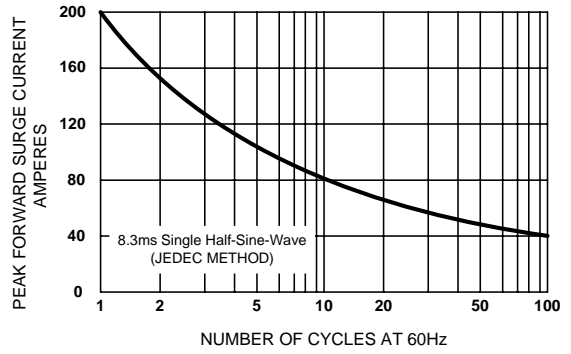


Figure 2. Maximum Non-repetitive Surge Current

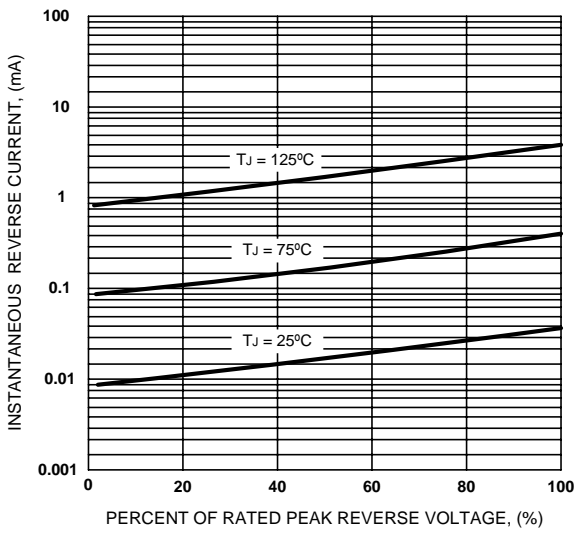


Figure 3. Typical Reverse Characteristics

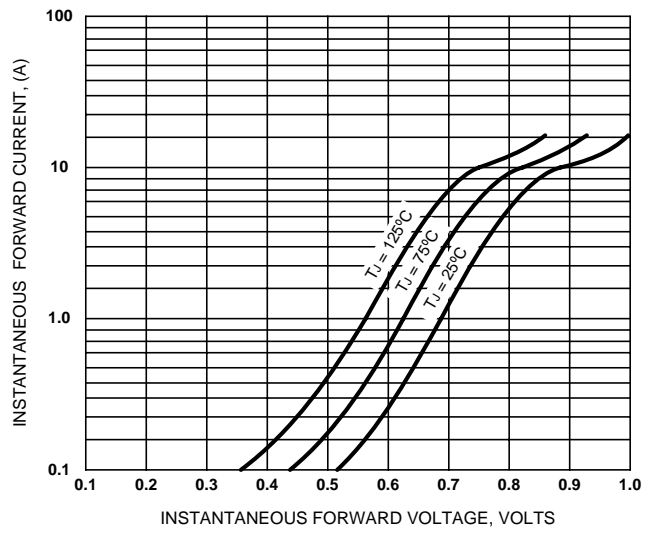


Figure 4. Typical Forward Characteristics

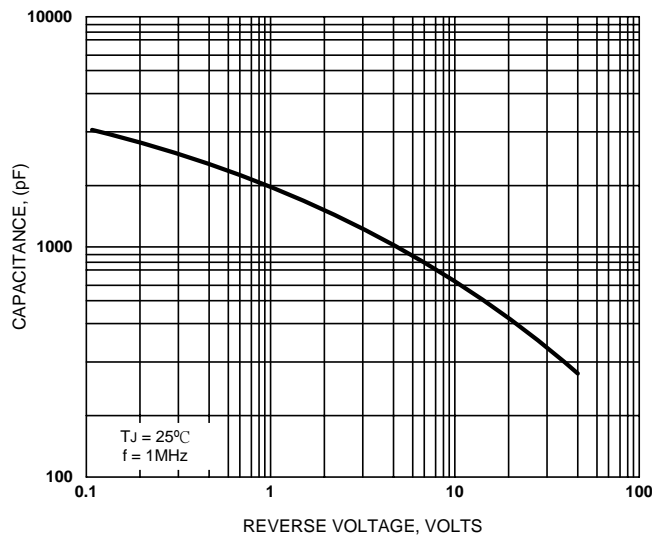
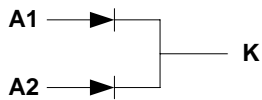
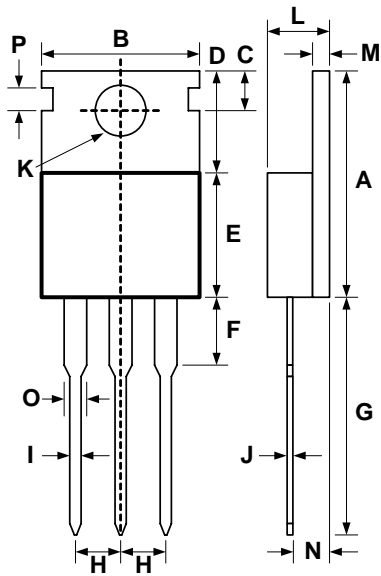


Figure 5. Typical Junction Capacitance

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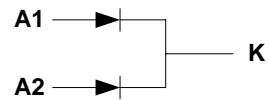
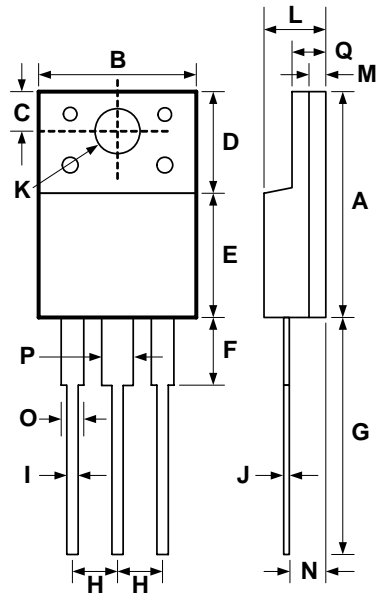
TO-220AB



DIM	DIMENSIONS				NOTE
	INCHES		MILLIMETERS		
	MIN	MAX	MIN	MAX	
A	.610	.630	15.5	16.00	
B	.390	.413	9.90	10.50	
C	.106	.126	2.70	3.20	
D	.228	.272	5.80	6.90	
E	.348	.372	8.85	9.45	
F	.102	.142	2.60	3.60	
G	.512	.551	13.00	14.00	
H	.093	.112	2.35	2.85	
I	.028	.037	0.70	0.95	
J	.016	.026	0.40	0.65	
K	.132	.152	3.35	3.85	
L	.169	.185	4.30	4.70	
M	.045	.057	1.15	1.45	
N	.089	.112	2.25	2.85	
O	.043	.055	1.10	1.40	
P	.055	.067	1.40	1.70	

MBR30V300FCTH

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DIM	DIMENSIONS				NOTE
	INCHES		MILLIMETERS		
	MIN	MAX	MIN	MAX	
A	.581	.600	14.75	15.25	
B	.386	.410	9.80	10.40	
C	.102	.122	2.60	3.10	
D	.228	.272	5.80	6.90	
E	.315	.339	8.00	8.60	
F	.138	.177	3.50	4.50	
G	.512	.551	13.00	14.00	
H	.093	.112	2.35	2.85	
I	.020	.030	0.50	0.75	
J	.020	.030	0.50	0.75	
K	.120	.140	3.05	3.55	
L	.169	.185	4.30	4.70	
M	.039	.051	1.00	1.30	
N	.089	.112	2.25	2.85	
O	.043	.055	1.10	1.40	
P	.059	.071	1.50	1.80	
Q	.114	.130	2.90	3.30	

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